IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. When strikethrough cannot easily be perceived, or when five or fewer characters are deleted, [[double brackets]] are used to show the deletion. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims 1 and 3 in accordance with the following:

1. (Currently Amended) A thin film forming method for plasmatizing a mixture gas, the mixture gas consisting of a monomer gas and an oxidizing reactive gas, and for forming a thin film on a surface of a substrate, the thin film being made of an oxide, the method comprising:

forming a first thin film by plasmatizing the mixture gas while varying a supply flow amount ratio of the monomer gas with respect to the reactive gas; and

forming a final thin film by increasing the supply flow amount ratio of the monomer gas with respect to the reactive gas after the forming of the first film, wherein

the forming of the first thin film is performed under a first condition that the supply flow amount ratio of the monomer gas with respect to the reactive gas decreases continuously from an initial value into a specific value of 0.05 or lower within 2 to 5 seconds at a constant speed, and the supply flow amount of the monomer gas is gradually reduced while the supply flow amount of the oxidizing reactive gas is maintained at a substantially fixed level; and

the forming of the final thin film is performed under a second condition that the supply flow amount ~~ratio~~ of the monomer gas increases at a constant speed and the supply flow amount of the reactive gas decreases at a constant speed, while the amount of the mixture gas is maintained at a substantially fixed level, the supply flow amount ratio of the monomer gas with respect to the reactive gas reaches 1000 or more, and the forming of the final thin film lasts for 1 to 3 seconds.

2. (Cancelled)

3. (Currently Amended) The thin film forming method according to claim 1, wherein an initial value of the supply flow amount ratio in the forming of the first thin film is in a range of 0.02 to 0.2.

4. (Cancelled).

5. (Previously Presented) The thin film forming method according to claim 1 or 3, wherein the mixture gas is plasmatized by controlling reflected power to be 10% or lower than supplied high frequency power, the reflected power being generated by supplying high frequency power of 100 MHz or lower to a high frequency electrode through an impedance matching network.

6-17. (Cancelled).